

# ZXTP25060BFH

## 60V, SOT23, PNP medium power transistor

### Summary

$BV_{(BR)CEX} > -100V$ ,  $BV_{(BR)CEO} > -60V$

$BV_{(BR)ECO} > -7V$  ;

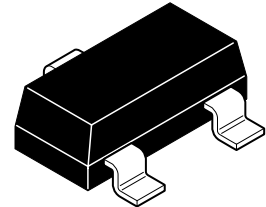
$I_{C(cont)} = -3A$ ;

$R_{CE(sat)} = 58\text{ m}\Omega$  typical;

$V_{CE(sat)} < -85mV @ -1A$  ;

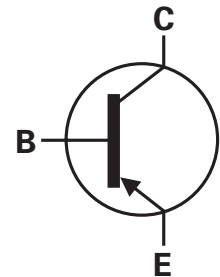
$P_D = 1.25W$

Complementary part number ZXTN25060BFH



### Description

Advanced process capability and package design have been used to maximize the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

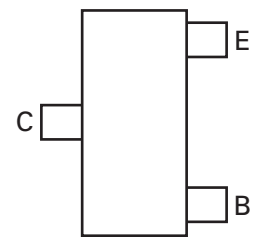


### Features

- Higher power dissipation SOT23 package
- High peak current
- Low saturation voltage
- 100V forward blocking voltage
- 7V reverse blocking voltage

### Applications

- MOSFET gate drivers
- Power switches
- Motor control



Pinout - top view

### Ordering information

Device	Reel size (inches)	Tape width	Quantity per reel
ZXTP25060BFHTA	7	8mm	3,000

### Device marking

028

# ZXTP25060BFH

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	$V_{CBO}$	-100	V
Collector-emitter voltage (forward blocking)	$V_{CEX}$	-100	V
Collector-emitter voltage	$V_{CEO}$	-60	V
Emitter-collector voltage (reverse blocking)	$V_{ECO}$	-7	V
Emitter-base voltage	$V_{EBO}$	-7	V
Continuous collector current <sup>(a)</sup>	$I_C$	-3	A
Peak pulse current	$I_{CM}$	-9	A
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(a)</sup> Linear derating factor	$P_D$	0.73 5.84	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(b)</sup> Linear derating factor	$P_D$	1.05 8.4	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(c)</sup> Linear derating factor	$P_D$	1.25 9.6	W mW/°C
Power dissipation at $T_A = 25^\circ\text{C}$ <sup>(d)</sup> Linear derating factor	$P_D$	1.81 14.5	W mW/°C
Operating and storage temperature range	$T_j, T_{stg}$	-55 to 150	°C

## Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\theta JA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\theta JA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\theta JA}$	69	°C/W

### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

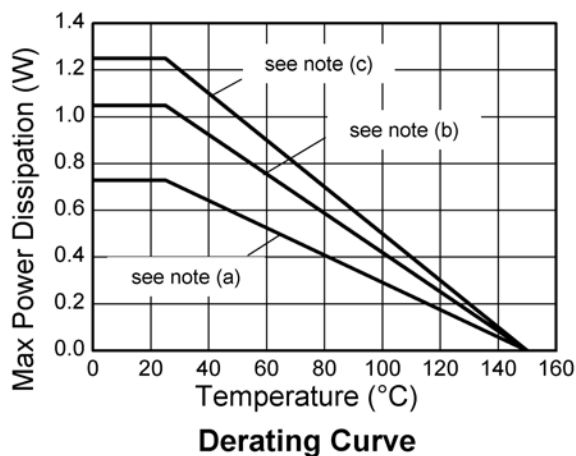
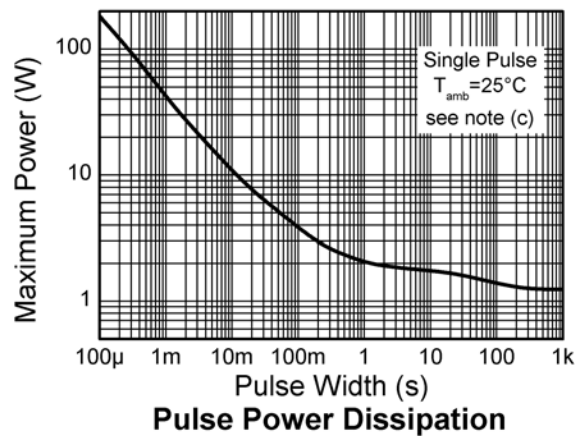
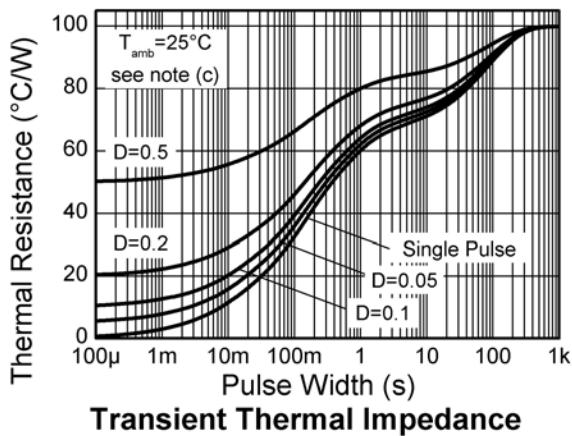
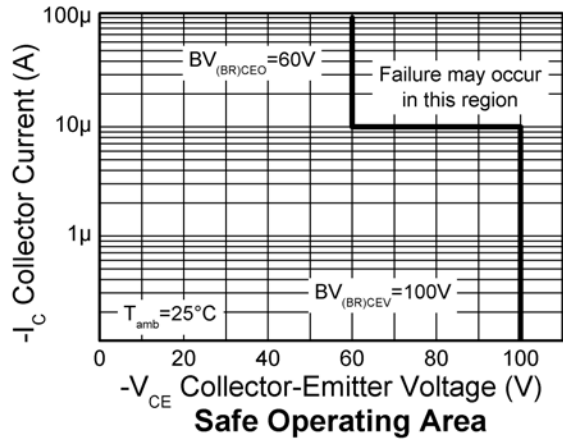
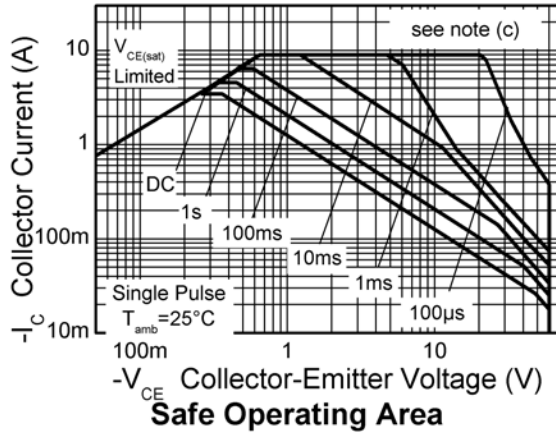
(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions.

(d) As (c) above measured at  $t < 5\text{secs}$

# ZXTP25060BFH

## Characteristics



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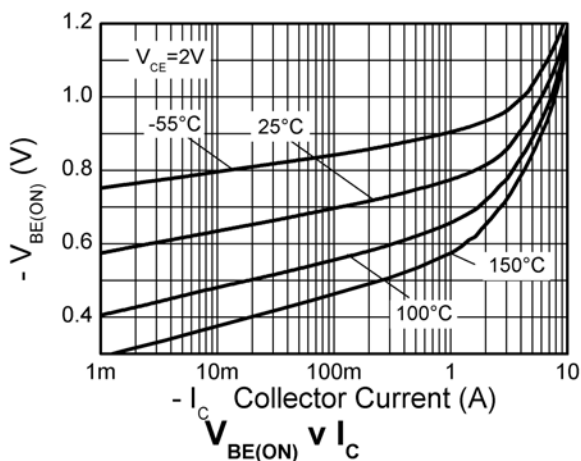
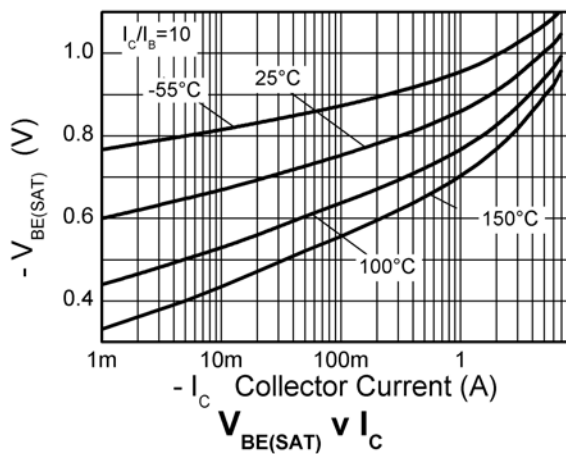
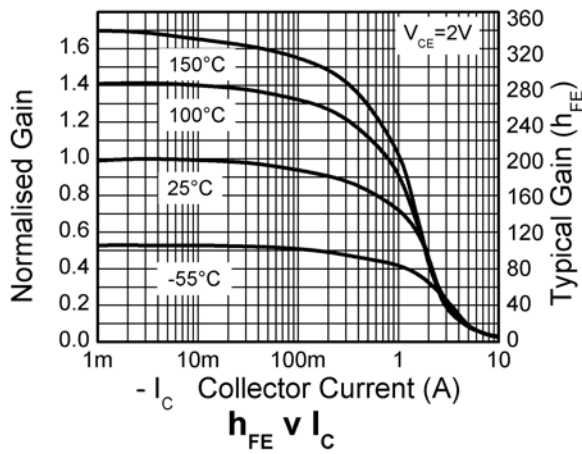
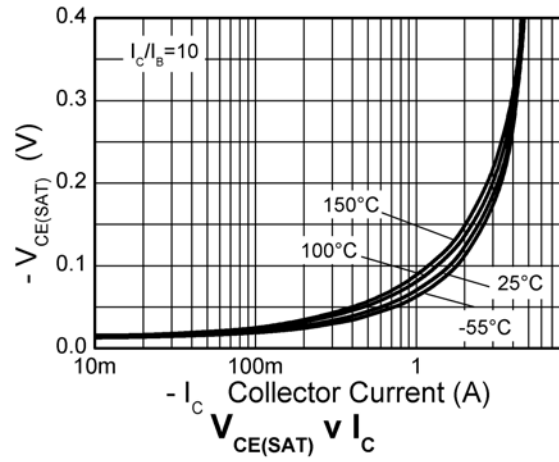
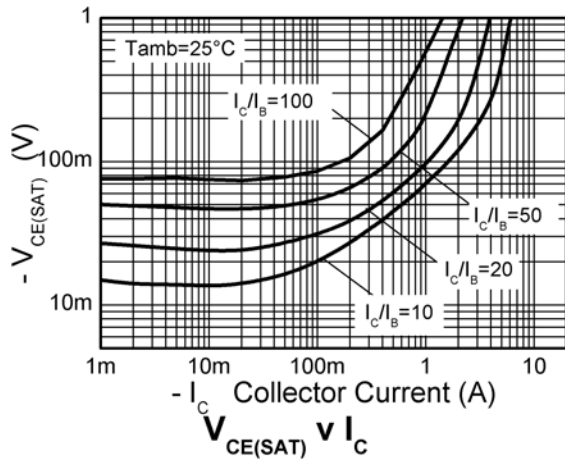
## Electrical characteristics (at $T_{AMB} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-100	-120		V	$I_C = -100\text{mA}$
Collector-emitter breakdown voltage (forward blocking)	$BV_{CEX}$ ,	-100	-120		V	$I_C = -100\text{mA}$ , $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Collector-emitter breakdown voltage (base open)	$BV_{CEO}$	-60	-80		V	$I_C = -10\text{mA}$ (*)
Emitter-collector breakdown voltage (reverse blocking)	$BV_{ECO}$	-7	-8.6		V	$I_E = -100\mu\text{A}$ (*)
Emitter-base breakdown voltage	$BV_{EBO}$	-7	-8.1		V	$I_E = -100\text{mA}$
Collector cut-off current	$I_{CBO}$		<-1	-50 -20	nA $\mu\text{A}$	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$ , $T_{AMB} = 100^{\circ}\text{C}$
Collector emitter cut-off current	$I_{CEX}$		-	-100	nA	$V_{CE} = -80\text{V}$ ; $R_{BE} < 1\text{k}\Omega$ or $-0.25\text{V} < V_{BE} < 1\text{V}$
Emitter cut-off current	$I_{EBO}$		<-1	-50	nA	$V_{EB} = -5.6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-45 -100 -70 -175	-55 -135 -85 -235	mV mV mV mV	$I_C = -0.5\text{A}$ , $I_B = -50\text{mA}$ (*) $I_C = -0.5\text{A}$ , $I_B = -10\text{mA}$ (*) $I_C = -1\text{A}$ , $I_B = -100\text{mA}$ (*) $I_C = -3\text{A}$ , $I_B = -300\text{mA}$ (*)
Base-emitter saturation voltage	$V_{BE(sat)}$		-940	-1040	mV	$I_C = -3\text{A}$ , $I_B = -300\text{mA}$ (*)
Base-emitter turn-on voltage	$V_{BE(on)}$		-830	-930	mV	$I_C = -3\text{A}$ , $V_{CE} = -2\text{V}$ (*)
Static forward current transfer ratio	$h_{FE}$	100 75 30	200 150 60	300		$I_C = -10\text{mA}$ , $V_{CE} = -2\text{V}$ (*) $I_C = -1\text{A}$ , $V_{CE} = -2\text{V}$ (*) $I_C = -3\text{A}$ , $V_{CE} = -2\text{V}$ (*)
Transition frequency	$f_T$		250		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -5\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{OBO}$		17.6	30	pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$ (*)
Turn-on time	$t_{(on)}$		26.5		ns	$V_{CC} = -10\text{V}$ . $I_C = -500\text{mA}$ ,
Turn-off time	$t_{(off)}$		291		ns	$I_{B1} = I_{B2} = -50\text{mA}$ .

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## Typical characteristics



# ZXTP25060BFH

## Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
A	2.67	3.05	0.105	0.120	H	0.33	0.51	0.013	0.020
B	1.20	1.40	0.047	0.055	K	0.01	0.10	0.0004	0.004
C	-	1.10	-	0.043	L	2.10	2.50	0.083	0.0985
D	0.37	0.53	0.015	0.021	M	0.45	0.64	0.018	0.025
F	0.085	0.15	0.0034	0.0059	N	0.95 NOM		0.0375 NOM	
G	1.90 NOM		0.075 NOM		-	-	-	-	-

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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